

REVISIONS

LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device type 02, case outline Y, and figure A-2. - ro	15-01-26	C. SAFFLE
B	Add device type 03. - ro	19-11-12	J. ESCHMEYER



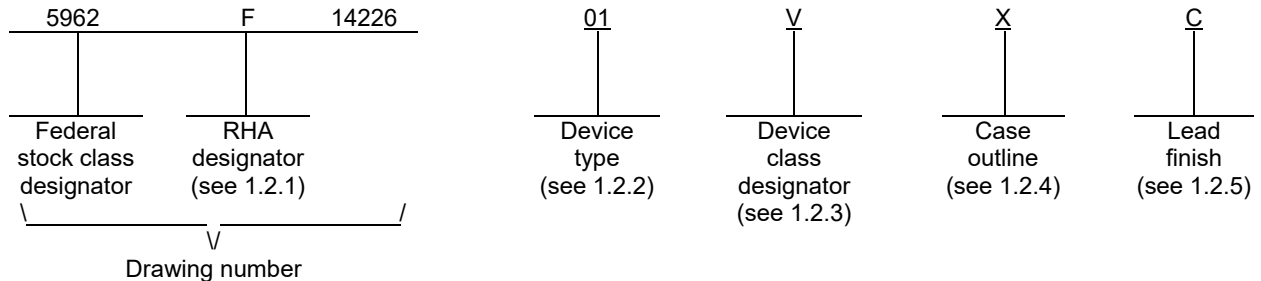
REV																				
SHEET																				
REV	B	B	B	B	B	B	B	B	B	B	B	B	B							
SHEET	15	16	17	18	19	20	21	22	23	24	25	26	27							
REV STATUS OF SHEETS	REV			B	B	B	B	B	B	B	B	B	B	B	B	B	B	B	B	B
	SHEET			1	2	3	4	5	6	7	8	9	10	11	12	13	14			

PMIC N/A	PREPARED BY RICK OFFICER	<p align="center">DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990 https://www.dla.mil/LandandMaritime</p> <p align="center">MICROCIRCUIT, LINEAR, PRECISION LOW POWER OPERATIONAL AMPLIFIERS, MONOLITHIC SILICON</p>																			
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p align="center">THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p>	CHECKED BY RAJESH PITHADIA																				
	APPROVED BY CHARLES F. SAFFLE																				
	DRAWING APPROVAL DATE 14-09-02																				
AMSC N/A	REVISION LEVEL B	SIZE A	CAGE CODE 67268	5962-14226																	
			SHEET		1 OF 27																

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device class Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL70419SEH	Quad, precision low power operational amplifier
02	ISL70219ASEH	Dual, precision low power operational amplifier
03	ISL73419SEH	Quad, precision low power operational amplifier

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

<u>Outline letter</u>	<u>Descriptive designator</u>	<u>Terminals</u>	<u>Package style</u>
X	See figure 1	14	Flat pack
Y	CDFP3-F10	10	Flat pack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 2

1.3 Absolute maximum ratings. 1/

Supply voltage (VS)	42 V
Supply voltage (LET = 86.4 MeV/(mg/cm ²)	36 V
Different input current	20 mA
Differential input voltage	20 V
Input voltage (VIN)	-VS - 0.5 V to +VS + 0.5 V
Input current for input voltage (> +VS or < -VS)	±20 mA
Output short circuit duration (1 output at a time)	Indefinite
Power dissipation (PD) :	
Case outline X:	
TA = +125°C	714 mW
TA = +25°C	3.571 W
Case outline Y:	
TA = +125°C	625 mW
TA = +25°C	3.125 W
Maximum junction temperature (Tj)	+150°C
Lead temperature (soldering, 10 seconds)	+300°C
Storage temperature range	-65°C to +150°C
Thermal resistance, junction-to-case (θJC) :	
Case outlines X and Y	8°C/W 2/
Thermal resistance, junction-to-ambient (θJA) :	
Case outline X	35°C/W 3/
Case outline Y	40°C/W 3/
Electrostatic discharge (ESD) rating:	
Human body model (HBM)	2 kV
Machine model (MM)	200 V
Charge device model (CDM)	750 V

1.4 Recommended operating conditions.

Supply voltage (VS) :	
Device types 01 and 03	10 V (±5 V) to 30 V (±15 V)
Device type 02	4.5 V (±2.25 V) to 36 V (±18 V)
Ambient operating temperature range (TA)	-55°C to +125°C

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ For θJC, the “case temperature” location is the center of the package underside.

3/ θJA is measured in free air with the component mounted on a high effective thermal conductivity test board with “direct attach” features.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 3

1.5 Radiation features.

Maximum total dose available (dose rate = 50 – 300 rad(Si)/s)	
Device types 01 and 02	300 krad(Si) <u>4/</u>
Maximum total dose available (dose rate ≤ 0.010 rad(Si)/s)	
Device types 01, 02 and 03	50 krad(Si) <u>4/ 5/</u>
Single event phenomenon (SEP):	
No Single event latchup (SEL) occurs at effective LET (see 4.4.4.2)	≤ 86 MeV/(mg/cm ²) <u>6/</u>
No Single event burnout (SEB) occurs at effective LET (see 4.4.4.2)	≤ 86 MeV/(mg/cm ²) <u>6/</u>
Single event transient (SET) observed that resulted in a recovery time not exceeding 10 μs (device type 01) and 15 μs (device type 02) at saturated cross section = 1.22 x 10 ⁻³ cm ² with effective LET (see 4.4.4.2)	60 MeV/(mg/cm ²) <u>6/</u>

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

ASTM INTERNATIONAL (ASTM)

ASTM F1192 - Standard Guide for the Measurement of Single Event Phenomena (SEP) from Heavy Ion Irradiation of semiconductor Devices.

(Copies of these documents are available online at <https://www.astm.org>.)

- 4/ Device types 01 and 02 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 300 krads(Si), and condition D to a maximum total dose of 50 krads(Si).
- 5/ Device type 03 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition D to a maximum total ionizing dose (TID) level of 50 krad(Si).
- 6/ Limits are characterized at initial qualification and after any design or process changes which may affect the SEP characteristics but are not production tested unless specified by the customer through the purchase order or contract. See manufacturer's SEE test report for more information.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 4

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.1.1 Microcircuit die. For the requirements of microcircuit die, see appendix A to this document.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table IA and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table IA.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 5

TABLE IA. Electrical performance characteristics.

Test	Symbol	Conditions <u>1/ 2/</u> -55°C ≤ TA ≤ +125°C device types 01, 03, VS = ±15 V, device type 02, VS = ±18 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Offset voltage	VOS		1	01, 02, 03		85	μV
			2,3			110	
			M,D,P,L,R,F		1		
Input bias current	IIB		1	01, 02	-2.5	2.5	nA
			2,3		-5	5	
			M,D,P,L,R,F		1	-15	
Input offset current	IOS		1	01, 02, 03	-2.5	2.5	nA
			2,3		-3	3	
			M,D,P,L,R,F		1	-10	
Input voltage range	VCM	Guaranteed by CMRR test	1,2,3	01, 03	-13	13	V
				02	-16	16	
Common mode rejection ratio	CMRR	VCM = -13 V to +13 V	1,2,3	01, 02, 03	120		dB
Power supply rejection ratio	PSRR	VS = ±2.25 V to ±20 V	1,2,3	01, 02, 03	120		dB
Open loop gain	AVOL	VO = -13 V to +13 V, RL = 10 kΩ to ground	4,5,6	01, 02, 03	3,000		V/mV
Output voltage high	VOH	RL = 10 kΩ to ground	1	01, 02, 03	VS - 1.5		V
			2, 3		VS - 1.8		
			M,D,P,L,R,F		1	VS - 1.8	
		RL = 2 kΩ to ground	1		VS - 1.7		
			2, 3		VS - 2.0		
			M,D,P,L,R,F		1	VS - 2.0	

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 6

TABLE IA. Electrical performance characteristics - Continued.

Test	Symbol	Conditions <u>1/2/</u> -55°C ≤ TA ≤ +125°C device types 01, 03, VS = ±15 V, device type 02, VS = ±18 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Output voltage low	VOL	RL = 10 kΩ to ground	1	01, 02, 03		-VS + 1.5	V
			2, 3			-VS + 1.8	
			M,D,P,L,R,F		1		
		RL = 2 kΩ to ground	1			-VS + 1.7	
			2, 3			-VS + 2.0	
			M,D,P,L,R,F		1		
Supply current / amplifier	IS		1	01, 03		0.53	mA
			2, 3			0.68	
			M,D,P,L,R,F		1		
			1	02		0.725	
			2, 3			0.85	
			M,D,P,L,R,F		1		
Supply voltage range	VS	Guaranteed by PSRR	1,2,3	01, 02, 03	±2.25	±20	V
Transient response							
Slew rate, VOUT 20% to 80%	SR	AV = 1, RL = 2 kΩ, VO = 4 VPP	4	01, 02, 03	0.3		V/μs
			5,6		0.2		
			M,D,P,L,R,F		1	0.2	
Rise time, 10% to 90% of VOUT	tr	AV = 1, VOUT = 50 mVP-P, RL = 10 kΩ to VCM	4	01, 02, 03		450	ns
			5,6			625	
			M,D,P,L,R,F		4		
Fall time, 90% to 10% of VOUT	tf	AV = 1, VOUT = 50 mVP-P, RL = 10 kΩ to VCM	4	01, 02, 03		600	ns
			5,6			700	
			M,D,P,L,R,F		4		
Positive overshoot	+OS	AV = 1, VOUT = 10 VP-P, Rf = 0 Ω, RL = 2 kΩ to VCM	4,5,6	01, 02, 03		33	%
Negative overshoot	-OS	AV = 1, VOUT = 10 VP-P, Rf = 0 Ω, RL = 2 kΩ to VCM	4,5,6	01, 02, 03		33	%

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 7

TABLE IA. Electrical performance characteristics - Continued.

Test	Symbol	Conditions <u>1/ 2/</u> -55°C ≤ T _A ≤ +125°C V _S = ±5 V, unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Offset voltage	V _{OS}		1	01, 02, 03		150	μV
			2,3			250	
			M,D,P,L,R,F		1		
Input bias current	I _{IB}		1	01, 02, 03	-2.5	2.5	nA
			2,3		-5	5	
			M,D,P,L,R,F		1	-15	
Input offset current	I _{OS}		1	01, 02, 03	-2.5	2.5	nA
			2,3		-3	3	
			M,D,P,L,R,F		1	-10	
Input voltage range	V _{CM}	Guaranteed by CMRR test	1,2,3	01, 02, 03	-3	3	V
Common mode rejection ratio	CMRR	V _{CM} = -3 V to +3 V	1,2,3	01, 02, 03	120		dB
Power supply rejection ratio	PSRR	V _S = ±2.25 V to ±5 V	1,2,3	01, 02, 03	120		dB
Open loop gain	A _{VOL}	V _O = -3 V to +3 V, R _L = 10 kΩ to ground	4,5,6	01, 02, 03	3,000		V/mV
Output voltage high	V _{OH}	R _L = 10 kΩ to ground	1	01, 02, 03	3.5		V
			2, 3		3.2		
			M,D,P,L,R,F		1	3.2	
		R _L = 2 kΩ to ground	1		3.3		
			2, 3		3.0		
			M,D,P,L,R,F		1	3.0	
Output voltage low	V _{OL}	R _L = 10 kΩ to ground	1	01, 02, 03		-3.5	V
			2, 3			-3.2	
			M,D,P,L,R,F		1		
		R _L = 2 kΩ to ground	1			-3.3	
			2, 3			-3.0	
			M,D,P,L,R,F		1		

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 8

TABLE IA. Electrical performance characteristics - Continued.

Test	Symbol	Conditions <u>1/2/</u> -55°C ≤ T _A ≤ +125°C V _S = ±5 V, unless otherwise specified	Group A subgroups	Device type	Limits		Unit		
					Min	Max			
Supply current / amplifier	I _S		1	01, 03		0.625	mA		
			2, 3			0.75			
			M,D,P,L,R,F		1			0.75	
				M,D,P,L,R,F	1	02			0.675
					2, 3				0.8
					1				0.8

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 9

TABLE IA. Electrical performance characteristics - Continued.

Test	Symbol	Conditions <u>1/ 2/</u> -55°C ≤ T _A ≤ +125°C V _S = ±2.25 V unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Offset voltage	V _{OS}		1	02		150	μV
			2,3			250	
			M,D,P,L,R,F		1	250	
Input bias current	I _{IB}		1	02	-2.5	2.5	nA
			2,3		-5	5	
			M,D,P,L,R,F		1	-15	
Input offset current	I _{OS}		1	02	-2.5	2.5	nA
			2,3		-3	3	
			M,D,P,L,R,F		1	-10	
Input voltage range	V _{CM}	Guaranteed by CMRR test	1,2,3	02	-0.25	0.25	V
Common mode rejection ratio	CMRR	V _{CM} = -3 V to +3 V	1,2,3	02	90		dB
Output voltage high	V _{OH}	R _L = 10 kΩ to ground	1	02	0.8		V
			2, 3		0.5		
			M,D,P,L,R,F		1	0.5	
		R _L = 2 kΩ to ground	1		0.75		
			2, 3		0.45		
			M,D,P,L,R,F		1	0.45	
Output voltage low	V _{OL}	R _L = 10 kΩ to ground	1	02		-0.8	V
			2, 3			-0.5	
			M,D,P,L,R,F		1		
		R _L = 2 kΩ to ground	1			-0.75	
			2, 3			-0.45	
			M,D,P,L,R,F		1		
Supply current / amplifier	I _S		1	02		0.675	mA
			2, 3			0.8	
			M,D,P,L,R,F		1		

See footnotes at end of table.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 10

TABLE IA. Electrical performance characteristics - Continued.

- 1/ Unless otherwise specified, VCM = 0 V and VO = 0 V.
- 2/ RHA device types 01 and 02 supplied to this drawing will meet all levels M, D, P, L, R, and F of irradiation for condition A and levels M, D, P, and L for condition D. However, this device type is only tested at the F level in accordance with MIL-STD-883, method 1019, condition A and tested at the L level in accordance with MIL-STD-883, method 1019, condition D (see 1.5 herein).
 RHA device type 03 supplied to this drawing will meet all levels M, D, P, and L of irradiation for condition D. However, device type 03 is only tested at the "L" level in accordance with MIL-STD-883, method 1019, condition D to TID level 50 krad(Si) (see 1.5 herein).

Pre and Post irradiation values are identical unless otherwise specified in Table IA. When performing post irradiation electrical measurements for any RHA level, TA = +25°C.

TABLE IB. SEP test limits. 1/ 2/ 3/

Device types	SEP	Temperature (TA)	Effective linear energy transfer (LET)
01, 02, 03	No SEL	125°C	LET ≤ 86 MeV/(mg/cm ²)
	No SEB	125°C	LET ≤ 86 MeV/(mg/cm ²)
	SET observed 4/	+25°C	LET = 60 MeV/(mg/cm ²)

- 1/ For single event phenomena (SEP) test conditions, see 4.4.4.2 herein.
- 2/ Technology characterization and model verification supplemented by in-line data may be used in lieu of end of line testing. Test plan must be approved by the technical review board and qualifying activity.
- 3/ Limits are characterized at initial qualification and after any design or process changes which may affect the SEP characteristics but are not production tested unless specified by the customer through the purchase order or contract. See manufacturer's SEE test report for more information.
- 4/ Single event transients (SET) observed that resulted in a recovery time not exceeding 10 μs (device types 01 and 03) and 15 μs (device type 02) at saturated cross section = 1.22 x 10⁻³ cm² with effective LET = 60 MeV/(mg/cm²).
 See manufacturer's SEE test report for more information

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 11

Case X

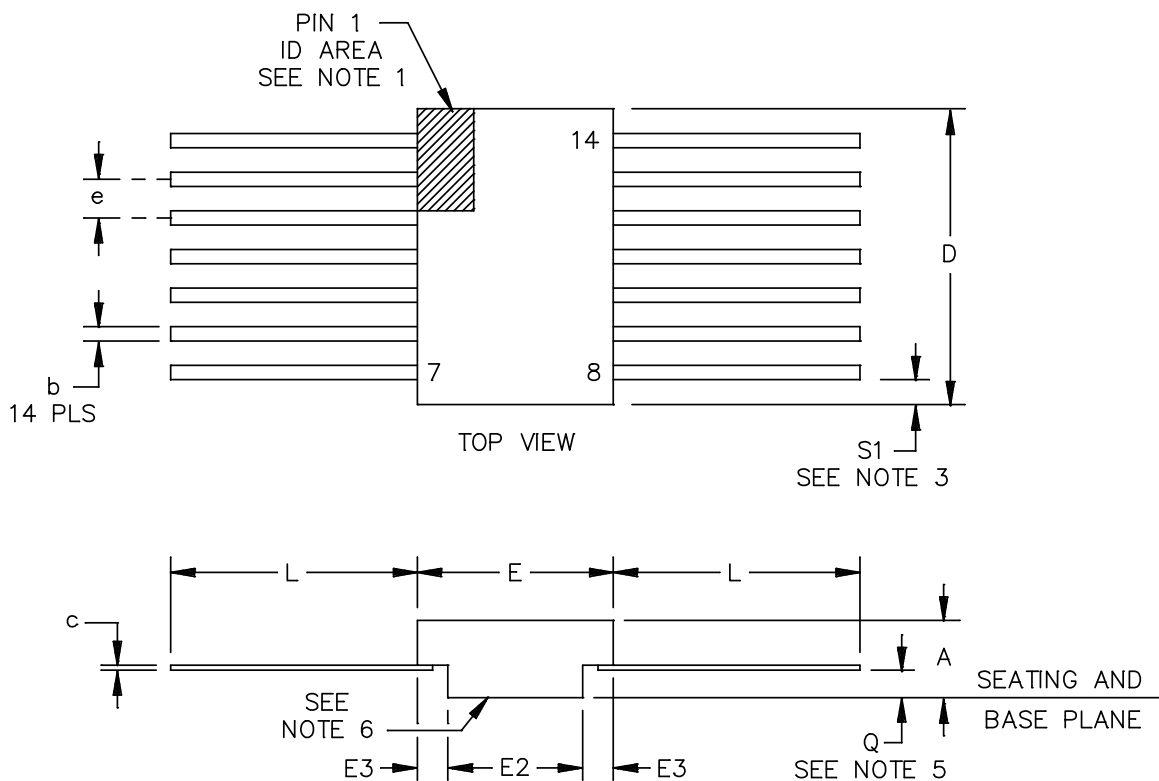


FIGURE 1. Case outline.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 12

Case X – continued.

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
A	0.085	0.115	2.16	2.92	
b	0.015	0.022	0.38	0.56	
c	0.004	0.009	0.10	0.23	
D	0.376	0.390	9.55	9.91	
e	0.050 BSC		1.27 BSC		
E	0.248	0.260	6.30	6.60	
E2	0.167	0.183	4.24	4.65	6
E3	0.03	---	0.76	---	
L	0.270	0.370	6.86	9.40	
Q	0.026	0.045	0.66	1.14	5
S1	0.005	---	0.13	---	3

NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown.
2. The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
3. Measure dimension at all four corners.
4. For bottom brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
5. Dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension minimum shall be reduced by 0.0015 inch (0.038 mm) maximum when solder dip lead finish is applied.
6. The bottom of the package is solderable metal surface.
7. Controlling dimensions are inch, millimeter dimensions are given for reference only.

FIGURE 1. Case outline - continued.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 13

Device types	01 and 03	
Case outline	X	
Terminal number	Terminal symbol	Description
1	OUTPUT A	Amplifier A output.
2	-INPUT A	Amplifier A inverting input.
3	+INPUT A	Amplifier A non-inverting input.
4	+Vs	Positive power supply.
5	+INPUT B	Amplifier B non-inverting input.
6	-INPUT B	Amplifier B inverting input.
7	OUTPUT B	Amplifier B output.
8	OUTPUT C	Amplifier C output.
9	-INPUT C	Amplifier C inverting input.
10	+INPUT C	Amplifier C non-inverting input.
11	-Vs	Negative power supply.
12	+INPUT D	Amplifier D non-inverting input.
13	-INPUT D	Amplifier D inverting input.
14	OUTPUT D	Amplifier D output.
EPAD	None	Unbiased, tied to package lid. The bottom of the package is a solderable metal surface.
Lid	None	Unbiased, tied to package EPAD.

FIGURE 2. Terminal connections.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 14

Device type	02	
Case outline	Y	
Terminal number	Terminal symbol	Description
1	OUTPUT A	Amplifier A output.
2	-INPUT A	Amplifier A inverting input.
3	+INPUT A	Amplifier A non-inverting input.
4	NC	No internal connection.
5	-Vs	Negative power supply.
6	LID	Pin connected to lid.
7	+INPUT B	Amplifier B non-inverting input.
8	-INPUT B	Amplifier B inverting input.
9	OUTPUT B	Amplifier B output.
10	+Vs	Positive power supply.

FIGURE 2. Terminal connections – continued.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 15

4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 16

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1, 4	1, 4
Final electrical parameters (see 4.2)	1, 2, 3, <u>1/</u> 4, 5, 6	1, 2, 3, <u>1/ 2/</u> 4, 5, 6
Group A test requirements (see 4.4)	1, 2, 3, 4, 5, 6	1, 2, 3, 4, 5, 6
Group C end-point electrical parameters (see 4.4)	1, 2, 3, 4, 5, 6	1, 2, 3, <u>2/</u> 4, 5, 6
Group D end-point electrical parameters (see 4.4)	1, 4	1, 4
Group E end-point electrical parameters (see 4.4)	1, 4	1, 4

1/ PDA applies to subgroup 1.

2/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be completed with reference to the previous electrical parameters.

TABLE IIB. Burn-in and operating life test delta parameters. T_A = +25°C. 1/

Parameters	Symbol	Conditions	Device types	Min	Max	Units
Offset voltage	V _{OS}	±15 V	01, 03	-40	40	μV
Input bias current	I _{IB}	±15 V	01, 03	-1	1	nA
Supply current	I _S	±15 V	01, 03	-500	500	μA
Offset voltage	V _{OS}	±18 V	02	-40	40	μV
Input bias current	I _{IB}	±18 V	02	-1	1	nA
Supply current	I _S	±18 V	02	-250	250	μA

1/ Deltas are performed at room temperature.

**STANDARD
MICROCIRCUIT DRAWING**
DLA LAND AND MARITIME
COLUMBUS, OHIO 43218-3990

SIZE
A

REVISION LEVEL
B

5962-14226

SHEET
17

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table IA at TA = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein. In addition, a low dose rate test shall be performed in accordance with MIL-STD-883 method 1019, condition D and as specified herein.

4.4.4.2 Single event phenomena (SEP). When specified in the purchase order or contract, SEP testing shall be performed on class V devices. SEP testing shall be performed on the Standard Evaluation Circuit (SEC) or alternate SEP test vehicle as approved by the qualifying activity at initial qualification and after any design or process changes which may affect the upset or latchup characteristics. Test four devices with zero failures. ASTM F1192 may be used as a guideline when performing SEP testing. The recommended test conditions for SEP are as follows:

- a. The ion beam angle of incidence shall be between normal to the die surface and 60° to the normal, inclusive (i.e. 0° ≤ angle ≤ 60°). No shadowing of the ion beam due to fixturing or package related affects is allowed.
- b. The fluence shall be ≥ 100 errors or ≥ 10⁷ ions/cm².
- c. The flux shall be between 10² and 10⁵ ions/cm²/s.
- d. The particle range shall be ≥ 20 micron in silicon.
- e. The test temperature shall be +125°C ±10% for SEB and SEL.
- f. For SEB test limits, see table IB herein.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 18

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

6.7 Additional information. When applicable, a copy of the following additional data shall be maintained and available from the device manufacturer:

- a. RHA test conditions (SEP).
- b. Number of burnouts (SEB).
- c. Number of latch-up (SEL).
- d. Number of transients (SET).

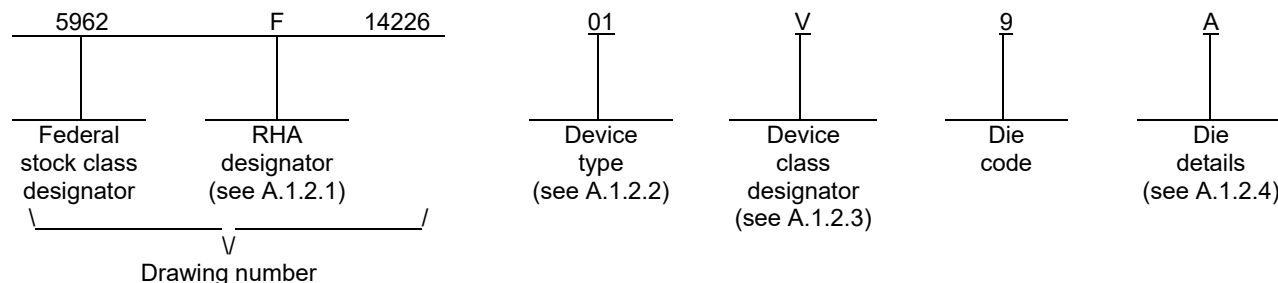
STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 19

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

A.1 SCOPE

A.1.1 Scope. This appendix establishes minimum requirements for microcircuit die to be supplied under the Qualified Manufacturers List (QML) Program. QML microcircuit die meeting the requirements of MIL-PRF-38535 and the manufacturers approved QM plan for use in monolithic microcircuits, multi-chip modules (MCMs), hybrids, electronic modules, or devices using chip and wire designs in accordance with MIL-PRF-38534 are specified herein. Two product assurance classes consisting of military high reliability (device class Q) and space application (device class V) are reflected in the Part or Identification Number (PIN). When available, a choice of Radiation Hardiness Assurance (RHA) levels are reflected in the PIN.

A.1.2 PIN. The PIN is as shown in the following example:



A.1.2.1 RHA designator. Device classes Q and V RHA identified die meet the MIL-PRF-38535 specified RHA levels. A dash (-) indicates a non-RHA die.

A.1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	ISL70419SEH	Quad, precision low power operational amplifier
02	ISL70219ASEH	Dual, precision low power operational amplifier
03	ISL73419SEH	Quad, precision low power operational amplifier

A.1.2.3 Device class designator.

<u>Device class</u>	<u>Device requirements documentation</u>
Q or V	Certification and qualification to the die requirements of MIL-PRF-38535

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 20

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

A.1.2.4 Die details. The die details designation is a unique letter which designates the die's physical dimensions, bonding pad location(s) and related electrical function(s), interface materials, and other assembly related information, for each product and variant supplied to this appendix.

A.1.2.4.1 Die physical dimensions.

<u>Die type</u>	<u>Figure number</u>
01, 03	A-1
02	A-2

A.1.2.4.2 Die bonding pad locations and electrical functions.

<u>Die type</u>	<u>Figure number</u>
01, 03	A-1
02	A-2

A.1.2.4.3 Interface materials.

<u>Die type</u>	<u>Figure number</u>
01, 03	A-1
02	A-2

A.1.2.4.4 Assembly related information.

<u>Die type</u>	<u>Figure number</u>
01, 03	A-1
02	A-2

A.1.3 Absolute maximum ratings. See paragraph 1.3 herein for details.

A.1.4 Recommended operating conditions. See paragraph 1.4 herein for details.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A	5962-14226
	REVISION LEVEL B	SHEET 21

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

A.2 APPLICABLE DOCUMENTS.

A.2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARD

MIL-STD-883 - Test Method Standard Microcircuits.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://quicksearch.dla.mil>.)

A.2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

A.3 REQUIREMENTS

A.3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

A.3.2 Design, construction and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein and the manufacturer's QM plan for device classes Q and V.

A.3.2.1 Die physical dimensions. The die physical dimensions shall be as specified in A.1.2.4.1 and on figures A-1 and A-2.

A.3.2.2 Die bonding pad locations and electrical functions. The die bonding pad locations and electrical functions shall be as specified in A.1.2.4.2 and on figures A-1 and A-2.

A.3.2.3 Interface materials. The interface materials for the die shall be as specified in A.1.2.4.3 and on figures A-1 and A-2.

A.3.2.4 Assembly related information. The assembly related information shall be as specified in A.1.2.4.4 and on figures A-1 and A-2.

A.3.2.5 Radiation exposure circuit. The radiation exposure circuit shall be as defined in paragraph 3.2.3 herein.

A.3.3 Electrical performance characteristics and post-irradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and post-irradiation parameter limits are as specified in table IA of the body of this document.

A.3.4 Electrical test requirements. The wafer probe test requirements shall include functional and parametric testing sufficient to make the packaged die capable of meeting the electrical performance requirements in table IA.

A.3.5 Marking. As a minimum, each unique lot of die, loaded in single or multiple stack of carriers, for shipment to a customer, shall be identified with the wafer lot number, the certification mark, the manufacturer's identification and the PIN listed in A.1.2 herein. The certification mark shall be a "QML" or "Q" as required by MIL-PRF-38535.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 22

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

A.3.6 Certification of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see A.6.4 herein). The certificate of compliance submitted to DLA Land and Maritime -VA prior to listing as an approved source of supply for this appendix shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and the requirements herein.

A.3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuit die delivered to this drawing.

A.4 VERIFICATION

A.4.1 Sampling and inspection. For device classes Q and V, die sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modifications in the QM plan shall not affect the form, fit, or function as described herein.

A.4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and as defined in the manufacturer's QM plan. As a minimum, it shall consist of:

- a. Wafer lot acceptance for class V product using the criteria defined in MIL-STD-883, method 5007.
- b. 100% wafer probe (see paragraph A.3.4 herein).
- c. 100% internal visual inspection to the applicable class Q or V criteria defined in MIL-STD-883, method 2010 or the alternate procedures allowed in MIL-STD-883, method 5004.

A.4.3 Conformance inspection.

A.4.3.1 Group E inspection. Group E inspection is required only for parts intended to be identified as radiation assured (see A.3.5 herein). RHA levels for device classes Q and V shall be as specified in MIL-PRF-38535. End point electrical testing of packaged die shall be as specified in table IIA herein. Group E tests and conditions are as specified in paragraphs 4.4.4, 4.4.4.1, and 4.4.4.2 herein.

A.5 DIE CARRIER

A.5.1 Die carrier requirements. The requirements for the die carrier shall be accordance with the manufacturer's QM plan or as specified in the purchase order by the acquiring activity. The die carrier shall provide adequate physical, mechanical and electrostatic protection.

A.6 NOTES

A.6.1 Intended use. Microcircuit die conforming to this drawing are intended for use in microcircuits built in accordance with MIL-PRF-38535 or MIL-PRF-38534 for government microcircuit applications (original equipment), design applications, and logistics purposes.

A.6.2 Comments. Comments on this appendix should be directed to DLA Land and Maritime -VA, Columbus, Ohio, 43218-3990 or telephone (614)-692-0540.

A.6.3 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

A.6.4 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed within MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see A.3.6 herein) to DLA Land and Maritime -VA and have agreed to this drawing.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 23

APPENDIX A
 APPENDIX A FORMS A PART OF SMD 5962-14226

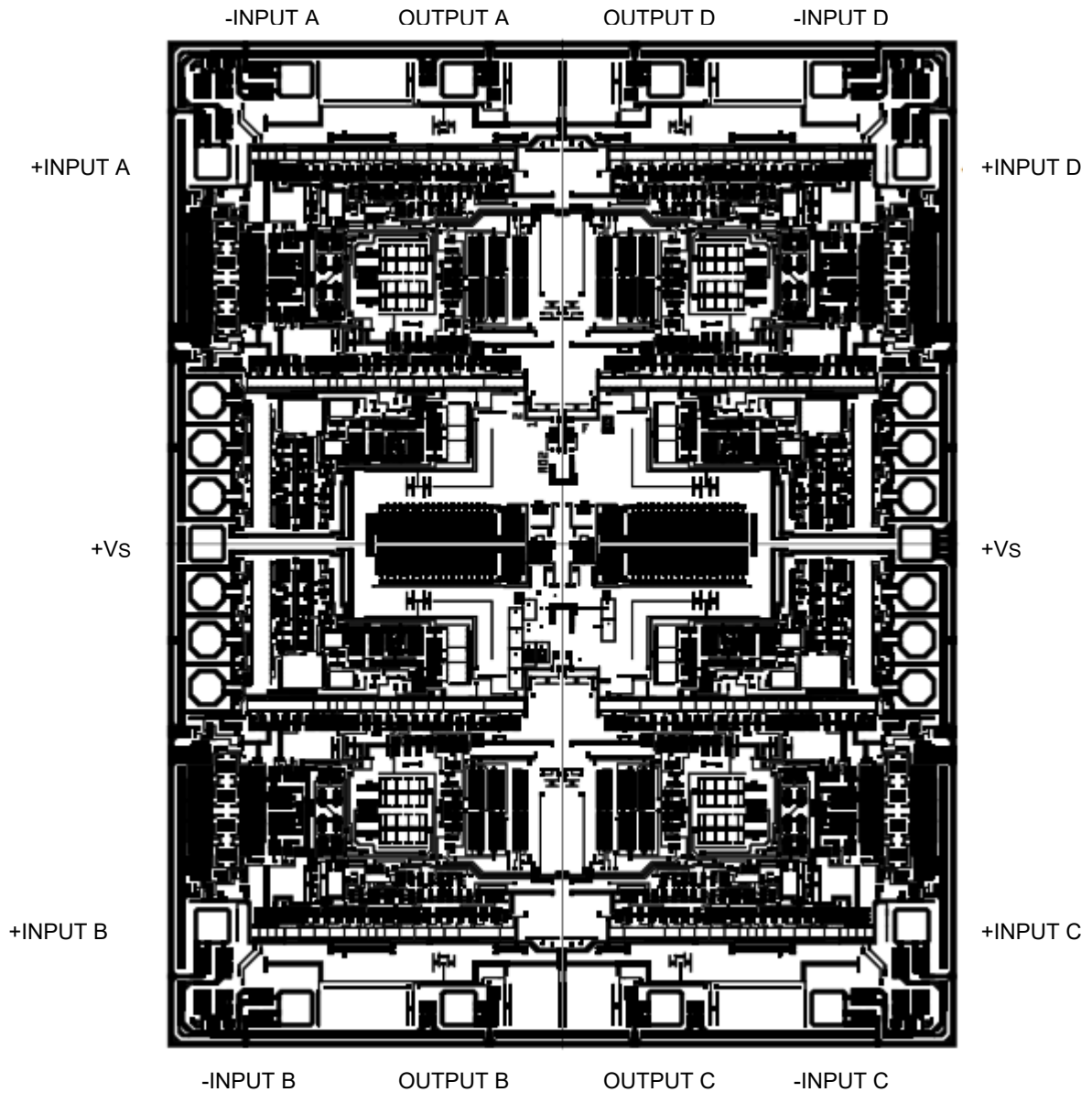


FIGURE A-1. Die bonding pad locations and electrical functions.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 24

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

Pad name	Pad number	X (μm)	Y (μm)	dX (μm)	dY (μm)	Bond wires per pad
OUTPUT A	3	-445.5	1308.5	70	70	1
-INPUT A	4	-815	1308.5	70	70	1
+INPUT A	5	-1040.5	1092	70	70	1
+VS	9	-1044	0	70	70	1
+INPUT B	13	-1040.5	-1092	70	70	1
-INPUT B	14	-815	-1308.5	70	70	1
OUTPUT B	15	-445.5	-1308.5	70	70	1
OUTPUT C	16	445.5	-1308.5	70	70	1
-INPUT C	17	815	-1308.5	70	70	1
+INPUT C	18	1040.5	-1092	70	70	1
-VS	22	1044	0	70	70	1
+INPUT D	26	1040.5	1092	70	70	1
-INPUT D	1	815	1308.5	70	70	1
OUTPUT D	2	445.5	1308.5	70	70	1

Note: Origin of coordinates is the center of the die.

Die bonding pad locations and electrical functions

Die physical dimensions.

Die size: 2406 μm x 2935 μm (95 mils x 116 mils)

Die thickness: 483 μm \pm 25 μm (19 mils \pm 1 mil)

Interface materials.

Top metallization: AlCu (99.5%/0.5%)

Thickness: 30 $\text{k}\text{\AA}$

Backside metallization: Bare Silicon

Glassivation.

Type: Nitrox

Thickness: 15 $\text{k}\text{\AA}$

Substrate: PR40 process: Bonded wafer dielectrically isolated complementary bipolar.

Assembly related information.

Substrate potential: Floating

Special assembly instructions: None

FIGURE A-1. Die bonding pad locations and electrical functions - continued.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 25

APPENDIX A
 APPENDIX A FORMS A PART OF SMD 5962-14226

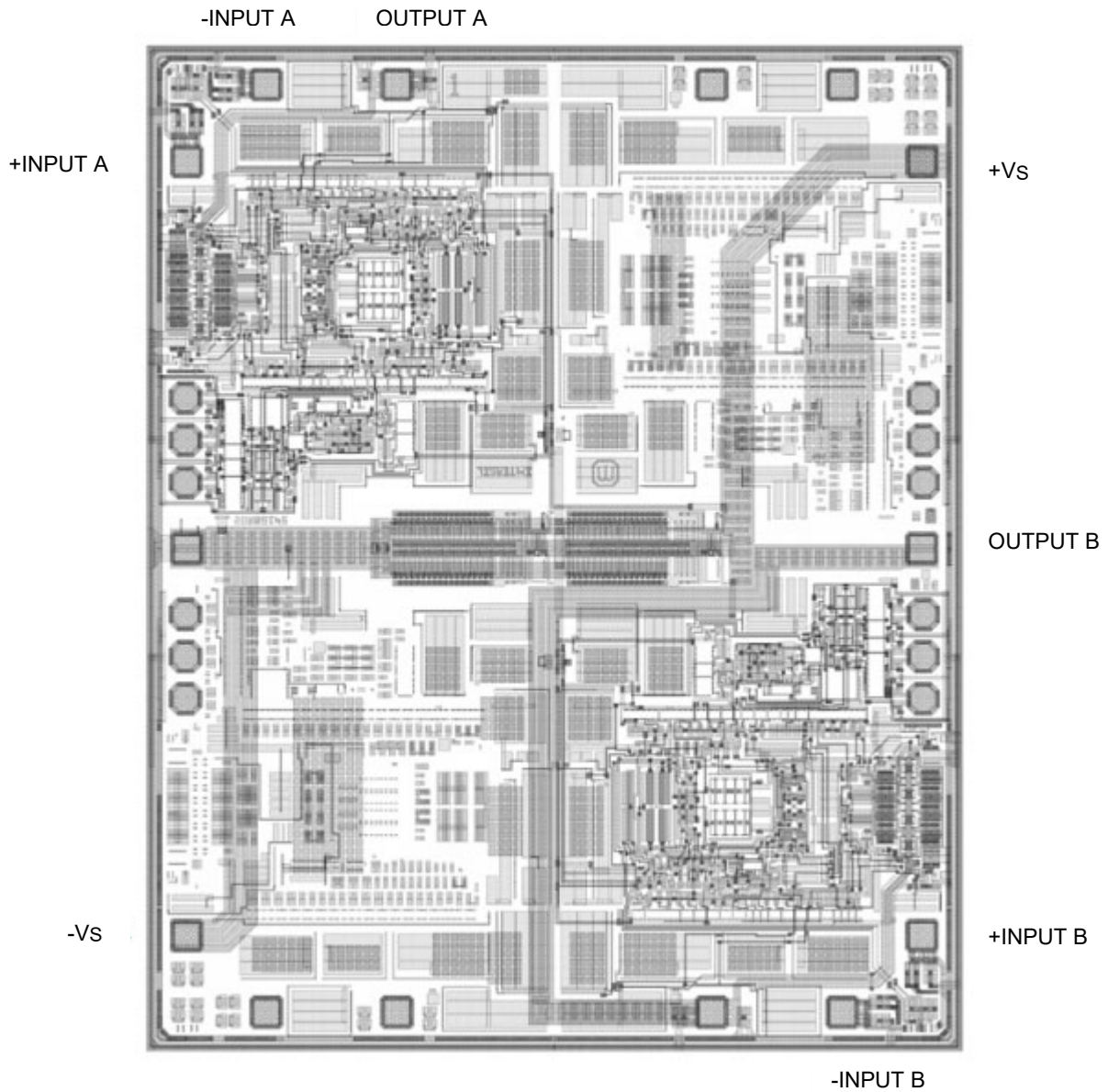


FIGURE A-2. Die bonding pad locations and electrical functions.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 26

APPENDIX A
APPENDIX A FORMS A PART OF SMD 5962-14226

Pad name	Pad number	X (μm)	Y (μm)	dX (μm)	dY (μm)	Bond wires per pad
OUTPUT B	1	2195.0	1418.0	70	70	1
+Vs	2	2195.0	2510.0	70	70	1
OUTPUT A	3	709.0	2727.0	70	70	1
-INPUT A	4	339.0	2727.0	70	70	1
+INPUT A	5	114.0	2510.0	70	70	1
-Vs	6	114.0	336.0	70	70	1
+INPUT B	7	2195.0	336.0	70	70	1
-INPUT B	8	1970.0	110.0	70	70	1

Note: Origin of coordinates is the bottom left corner of the die

Die physical dimensions.

Die size: 2406 μm x 2935 μm (95 mils x 116 mils)

Die thickness: 483 μm \pm 25 μm (19 mils \pm 1 mil)

Interface materials.

Top metallization: AlCu (99.5%/0.5%)

Thickness: 30 kÅ

Backside metallization: Bare silicon

Glassivation.

Type: Nitrox

Thickness: 15 kÅ

Substrate: PR40 process: Bonded wafer dielectrically isolated complementary bipolar.

Assembly related information.

Substrate potential: Floating

Special assembly instructions: None

FIGURE A-2. Die bonding pad locations and electrical functions - continued.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-14226
		REVISION LEVEL B	SHEET 27

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 19-11-12

Approved sources of supply for SMD 5962-14226 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <https://landandmaritimeapps.dla.mil/programs/smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962F1422601VXC	34371	ISL70419SEHVF
5962F1422601V9A	34371	ISL70419SEHVX
5962F1422602VYC	34371	ISL70219ASEHVF
5962F1422602V9A	34371	ISL70219ASEHVX
5962L1422603VXC	34371	ISL73419SEHVF
5962L1422603V9A	34371	ISL73419SEHVX

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

34371

Vendor name and address

Renesas Electronics America, Inc.
1650 Robert J. Conlan Blvd. NE
Palm Bay, FL 32905-3406

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.